









SN74AHC244Q

SGDS017A - FEBRUARY 2002 - REVISED APRIL 2023

SN74AHC244Q Octal Buffer/driver with 3-State Outputs

1 Features

- Q devices meet automotive performance requirements
- Customer-specific configuration control can be supported along with major-change approval
- EPIC™ (Enhanced-Performance Implanted CMOS) process
- Operating range of 2 V to 5.5 V V_{CC}
- Latch-Up performance exceeds 250 mA per JESD

2 Applications

- Enable or disable a digital signal
- · Eliminate slow or noisy input signals
- Hold a signal during controller reset
- · Debounce a switch

3 Description

This octal buffer/driver is designed specifically to improve the performance and density of 3-state memory-address drivers, clock drivers, and busoriented receivers and transmitters.

Package Information

PART NUMBER	PACKAGE ⁽¹⁾	BODY SIZE (NOM)
SN74AHC14Q-Q1	D (SOIC, 14)	8.65 mm × 3.9 mm
	PW (TSSOP, 14)	5 mm × 4.4 mm

 Package drawings, standard packing quantities, thermal data, symbolization, and PCB design guidelines are available at www.ti.com/sc/package.



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4 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

Changes from Revision * (February 2002) to Revision A (April 2023)

Page

Added Applications, Package Information table, Pin Functions table, ESD Ratings table, Thermal Information table, Device Functional Modes, Application and Implementation section, Power Supply Recommendations section, Layout section, Device and Documentation Support section, and Mechanical, Packaging, and Orderable Information section.



5 Function Table

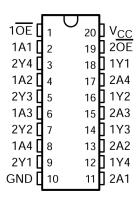


Figure 5-1. DW or PW Package (Top View)

Table 5-1. Pin Functions

	PIN		Table 3-1. Fill I diretions
NO.	NAME I/O NAME I/O NAME I O O O O O O O O O	DESCRIPTION	
1	1 ŌE	I	Output Enable 1
2	1A1	I	1A1 Input
3	2Y4	0	2Y4 Output
4	1A2	I	1A2 Input
5	2Y3	0	2Y3 Output
6	1A3	I	1A3 Input
7	2Y2	0	2Y2 Output
8	1A4	I	1A4 Input
9	2Y1	0	2Y1 Output
10	GND	_	Ground pin
11	2A1	I	2A1 Input
12	1Y4	0	1Y4 Output
13	2A2	I	2A2 Input
14	1Y3	0	1Y3 Output
15	2A3	I	2A3 Input
16	1Y2	0	1Y2 Output
17	2A4	I	2A4 Input
18	1Y1	0	1Y1 Output
19	2 OE	I	Output Enable 2
20	VCC	_	Power Pin



6 Specifications

6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)1

		MIN	MAX	UNIT
V _{CC}	Supply voltage range	-0.5	7	V
V _I ²	Input voltage range	-0.5	7	V
V _O ²	Output voltage range	-0.5	V _{CC} + 0.5	V
I _{IK} (V _I < 0)	Input clamp current		-20	mA
I_{OK} (V_O < 0 or V_O > V_{CC})	Output clamp current		±20	mA
$I_O (V_O = 0 \text{ to } V_{CC})$	Continuous output current		±25	mA
V _{CC} or GND	Continuous current		±50	mA
T _{stg}	Storage temperature range	-65	150	°C

- 1. Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
- 2. The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

6.2 ESD Ratings

			VALUE	UNIT
		Human-Body Model (A114-A) ⁽¹⁾	±1500	
V _(ESD)	Electrostatic discharge	Charged device model (CDM), per JEDEC specification JESD22-C101, all pins ⁽²⁾	±1000	V
		Machine Model (A115-A)	±200	

- (1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
- (2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

6.3 Recommended Operating Conditions

(see Note(1))

			MIN	MAX	UNIT	
V _{CC}	Supply voltage		2	5.5	V	
		V _{CC} = 2 V	1.5			
V _{IH}	High-level input voltage	V _{CC} = 3 V	2.1		V	
		V _{CC} = 5.5 V	3.85			
		V _{CC} = 2 V		0.5		
V _{IL}	Low-level input voltage	V _{CC} = 3 V		0.9	V	
		V _{CC} = 5.5 V		1.65		
VI	Input voltage	·	0	5.5	V	
Vo	Output voltage		0	V _{CC}	V	
		V _{CC} = 2 V		-50	μΑ	
I _{OH}	High-level output current	$V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V}$		-4	mA	
		V _{CC} = 5 V ± 0.5 V		-8	IIIA	
		V _{CC} = 2 V		50	μΑ	
I _{OL}	Low-level output current	$V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V}$		4	mA	
		$V_{CC} = 5 V \pm 0.5 V$		8	IIIA	
Δt/Δν	Input transition rise or fall rate	$V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V}$		100	ns/V	
ΔυΔν	input transition rise of fall fate	V _{CC} = 5 V ± 0.5 V		20	115/V	

(see Note⁽¹⁾)

		MIN	MAX	UNIT
T _A	Operating free-air temperature	-40	125	°C

⁽¹⁾ All unused inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, *Implications of Slow or Floating CMOS Inputs*, literature number SCBA004.

6.4 Thermal Information

		SN74AH	C244Q	
	THERMAL METRIC ⁽¹⁾	DW	PW	UNIT
		20 PINS	20 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	58	83	°C/W

⁽¹⁾ For more information about traditional and new thermal metrics, see the IC Package Thermal Metrics application report, SPRA953.

6.5 Electrical Characteristics

over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS			= 25 °C		MIN	MAX	UNIT
PARAMETER	TEST CONDITIONS	V _{cc}	MIN	TYP	MAX	IVIIIN	WAX	UNII
		2 V	1.9	2		1.9		
	I _{OH} = -50 μA	3 V	2.9	3		2.9		
V _{OH}		4.5 V	4.4	4.5		4.4		V
	I _{OH} = -4 mA	3 V	2.58			2.48		
	I _{OH} = -8 mA	4.5 V	3.94			3.8		
		2 V			0.1		0.1	
	I _{OL} = 50 μA	3 V			0.1		0.1	
V_{OL}		4.5 V			0.1		0.1	V
	I _{OL} = 4 mA	3 V			0.36		0.5	
	I _{OL} = 8 mA	4.5 V			0.36		0.5	
I _I	V _I = 5.5 V or GND	0 V to 5.5 V			±0.1		±1	μA
I _{OZ}	$V_O = V_{CC}$ or GND, $V_I (\overline{OE}) = V_{IL}$ or V_{IH}	5.5 V			±0.25		±2.5	μA
I _{cc}	$V_I = V_{CC}$ or GND, $I_O = 0$	5.5 V			4		40	μA
Ci	V _I = V _{CC} or GND	5 V		2	10			pF
Co	V _O = V _{CC} or GND	5 V		3.5				pF

6.6 Switching Characteristics, V_{CC} = 3.3 V ± 0.3 V

over recommended operating free-air temperature range, $V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V}$ (unless otherwise noted) (see Figure 7-1)

PARAMETER	FROM (INPUT)	то	LOAD CAPACITANCE	TA	= 25°C		MIN	MAX	UNIT
PARAMETER	PROW (INPUT)	(OUTPUT)	LOAD CAPACITANCE	MIN	TYP	MAX	IVIIIN	IVIAA	UNIT
t _{PLH}	A	Y	C _L = 15 pF		5.8	8.4	1	10	ns
t _{PHL}	A	ı	CL = 13 μr		5.8	8.4	1	10	115
t _{PZH}	- OE	Y	C _L = 15 pF		6.6	10.6	1	12.5	ne
t _{PZL}		ı	CL = 13 μr		6.6	10.6	1	12.5	ns
t _{PHZ}	ŌĒ	Y	C _L = 15 pF		5	9.7	1	11	ne
t _{PLZ}	OL .	ı	C _L = 13 μr		5	9.7	1	11	ns
t _{PLH}	A	Y	C _L = 50 pF		8.3	11.9	1	13.5	no
t _{PHL}		Ĭ	CL = 50 pr		8.3	11.9	1	13.5	ns
t _{PZH}	ŌĒ	Y	C _L = 50 pF		9.1	14.1	1	16	ne
t _{PZL}		ľ	OL – 30 PF		9.1	14.1	1	16	ns



over recommended operating free-air temperature range, V_{CC} = 3.3 V ± 0.3 V (unless otherwise noted) (see Figure 7-1)

PARAMETER	EDOM (INDIIT)	то	LOAD CAPACITANCE	TA	= 25°C		MIN	MAX	UNIT
PARAMETER	FROM (INPUT)	(OUTPUT)	LOAD CAPACITANCE	MIN	TYP	MAX	IVIIN IVIA	IVIAA	UNIT
t _{PHZ}	ŌĒ	V	C ₁ = 50 pF		10.3	14	1	16	no
t_{PLZ}	OE .	Ţ	OL - 30 PF		10.3	14	1	16	ns

6.7 Switching Characteristics, V_{CC} = 5 V ± 0.5 V

over recommended operating free-air temperature range, $V_{CC} = 5 \text{ V} \pm 0.5 \text{ V}$ (unless otherwise noted) (see Figure 7-1)

DADAMETED	EDOM (INDUIT)	TO (OUTPUT) LOAD	T,	= 25°C		NAINI	MAY	LINUT	
PARAMETER	FROM (INPUT)	10 (001701)	CAPACITANCE	MIN	TYP	MAX	MIN	MAX	UNIT
t _{PLH}	А	Y	C _L = 15 pF		3.9	5.5	1	6.5	ns
t _{PHL}		1	C _L = 13 μι		3.9	5.5	1	6.5	115
t _{PZH}	- ŌE	Υ	C _L = 15 pF		4.7	7.3	1	8.5	no
t _{PZL}	- OE	1	CL = 15 pr		4.7	7.3	1	8.5	ns
t _{PHZ}	- ŌĒ	Y	C _L = 15 pF		5	7.2	1	8.5	no
t _{PLZ}		1	CL = 15 pr		5	7.2	1	8.5	ns
t _{PLH}	- A	Y	C _L = 50 pF		5.4	7.5	1	8.5	20
t _{PHL}	7	1	C _L = 50 pr		5.4	7.5	1	8.5	ns
t _{PZH}	- ŌE	Y	C = 50 pF		6.2	9.3	1	10.5	20
t _{PZL}	- OE	f	$C_L = 50 pF$		6.2	9.3	1	10.5	ns
t _{PHZ}	- ŌĒ	Y	C = 50 pE		6.7	9.2	1	10.5	no
t _{PLZ}	- OE	f	$C_L = 50 pF$		6.7	9.2	1	10.5	ns

6.8 Noise Characteristics

 $V_{CC} = 5 \text{ V}, C_1 = 50 \text{ pF}, T_A = 25^{\circ}\text{C}$ (1)

<u>v(()</u>	7, OL 00 PI, TA 20 0				
	PARAMETER	MIN	TYP	MAX	UNIT
V _{OL(P)}	Quiet output, maximum dynamic V _{OL}		0.5		V
V _{OL(V)}	Quiet output, minimum dynamic V _{OL}		-0.2		V
V _{OH(V)}	Quiet output, minimum dynamic V _{OH}		4.8		V
V _{IH(D)}	High-level dynamic input voltage	3.5			V
V _{IL(D)}	Low-level dynamic input voltage			1.5	V

⁽¹⁾ Characteristics are for surface-mount packages only.

6.9 Operating Characteristics

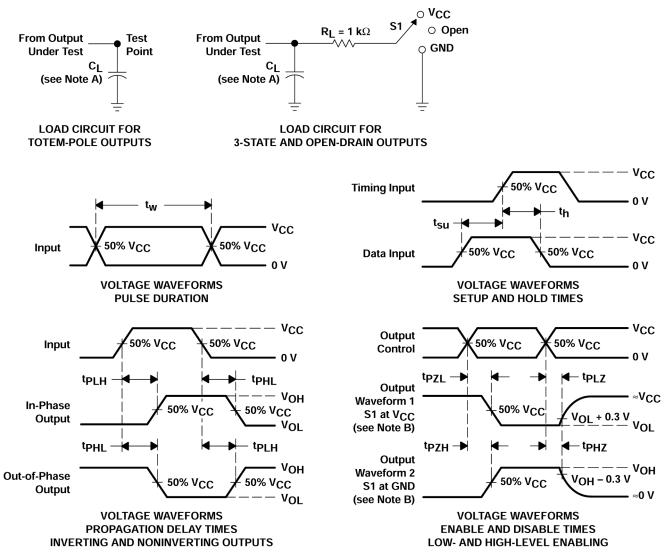
 $V_{CC} = 5 \text{ V}, T_A = 25^{\circ}\text{C}$

	PARAMETER	TEST CONDITIONS	TYP	UNIT
C _{pd}	Power dissipation capacitance	No load, f = 1 MHz	8.6	pF

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7 Parameter Measurement Information



- A. C_L includes probe and jig capacitance.
- B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
- C. All input pulses are supplied by generators having the following characteristics: PRR \leq 1 MHz, $Z_O = 50 \Omega$, $t_r \leq$ 3 ns, $t_f \leq$ 3 ns.
- D. The outputs are measured one at a time with one input transition per measurement.

Figure 7-1. Load Circuit and Voltage Waveforms

TEST	S1
t _{PLH} /t _{PHL}	Open
t _{PLZ} /t _{PZL}	V _{CC}
t _{PHZ} /t _{PZH}	GND
Open Drain	V _{CC}

8 Detailed Description

8.1 Overview

The SN74AHC244Q is organized as two 4-bit buffers/line drivers with separate output-enable (\overline{OE}) inputs. When \overline{OE} is low, the device passes data from the A inputs to the Y outputs. When \overline{OE} is high, the outputs are in the high-impedance state.

To ensure the high-impedance state during power up or power down, $\overline{\text{OE}}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

8.2 Functional Block Diagram

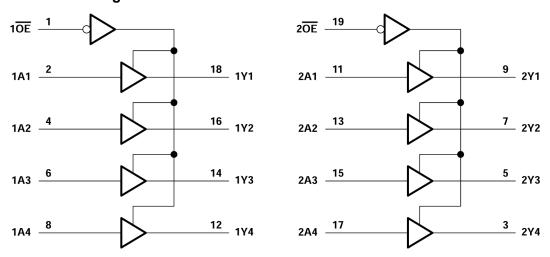


Figure 8-1. Logic Diagram (Positive Logic)

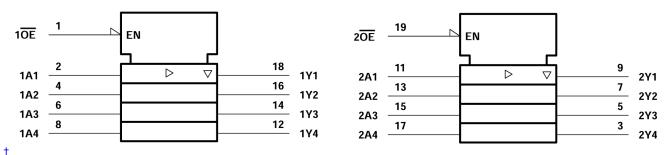


Figure 8-2. Logic Symbol

8.3 Device Functional Modes

Table 8-1. Function Table (Each 4-Bit Buffer/Driver)

INPUTS	OUTPUT	
ŌĒ	Α	Y
L	Н	Н
L	L	L
Н	X	Z

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[†] This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.



9 Application and Implementation

Note

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes, as well as validating and testing their design implementation to confirm system functionality.

9.1 Power Supply Recommendations

The power supply can be any voltage between the MIN and MAX supply voltage rating located in the Section 6.3 table.

Each VCC pin should have a good bypass capacitor to prevent power disturbance. For devices with a single supply, 0.1 μ f is recommended; if there are multiple VCC pins, then 0.01 μ f or 0.022 μ f is recommended for each power pin. It is acceptable to parallel multiple bypass caps to reject different frequencies of noise. A 0.1 μ f and a 1 μ f are commonly used in parallel. The bypass capacitor should be installed as close to the power pin as possible for best results.

9.2 Layout

9.2.1 Layout Guidelines

When using multiple-bit logic devices, inputs should never float.

In many cases, functions or parts of functions of digital logic devices are unused, for example, when only two inputs of a triple-input AND gate are used or only 3 of the 4 buffer gates are used. Such input pins should not be left unconnected because the undefined voltages at the outside connections result in undefined operational states. Layout Diagram specifies the rules that must be observed under all circumstances. All unused inputs of digital logic devices must be connected to a high or low bias to prevent them from floating. The logic level that should be applied to any particular unused input depends on the function of the device. Generally they will be tied to GND or V_{CC} , whichever makes more sense or is more convenient. It is generally acceptable to float outputs, unless the part is a transceiver. If the transceiver has an output enable pin, it will disable the output section of the part when asserted. This will not disable the input section of the I/Os, so they cannot float when disabled.



9.2.1.1 Layout Example

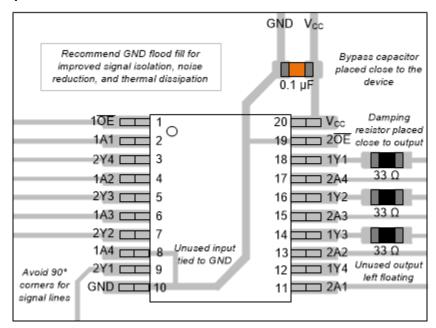


Figure 9-1. Layout Diagram



10 Device and Documentation Support

10.1 Documentation Support

10.1.1 Related Documentation

The table below lists quick access links. Categories include technical documents, support and community resources, tools and software, and quick access to sample or buy.

Table 10-1. Related Links

PARTS	PRODUCT FOLDER	SAMPLE & BUY	TECHNICAL DOCUMENTS	TOOLS & SOFTWARE	SUPPORT & COMMUNITY	
SN74AHC244Q	Click here	Click here	Click here	Click here	Click here	

10.2 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. Click on *Subscribe to updates* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

10.3 Support Resources

TI E2E[™] support forums are an engineer's go-to source for fast, verified answers and design help — straight from the experts. Search existing answers or ask your own question to get the quick design help you need.

Linked content is provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

10.4 Trademarks

TI E2E™ is a trademark of Texas Instruments.

All trademarks are the property of their respective owners.

10.5 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

10.6 Glossary

TI Glossary

This glossary lists and explains terms, acronyms, and definitions.



11 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

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PACKAGING INFORMATION

Orderable Device	Status	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead finish/ Ball material	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
							(6)				
SN74AHC244QDWRG4	ACTIVE	SOIC	DW	20	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM		AHC244Q	Samples
SN74AHC244QDWRG4Q1	ACTIVE	SOIC	DW	20	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM		AHC244Q1	Samples
SN74AHC244QPWR	ACTIVE	TSSOP	PW	20	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	HA244Q	Samples
SN74AHC244QPWRG4	ACTIVE	TSSOP	PW	20	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM		HA244Q	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

- (3) MSL, Peak Temp. The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead finish/Ball material Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

Important Information and Disclaimer: The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and



PACKAGE OPTION ADDENDUM

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continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

PACKAGE MATERIALS INFORMATION

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TAPE AND REEL INFORMATION





A0	Dimension designed to accommodate the component width
В0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN74AHC244QDWRG4	SOIC	DW	20	2000	330.0	24.4	10.8	13.3	2.7	12.0	24.0	Q1
SN74AHC244QDWRG4Q1	SOIC	DW	20	2000	330.0	24.4	10.8	13.3	2.7	12.0	24.0	Q1
SN74AHC244QPWR	TSSOP	PW	20	2000	330.0	16.4	6.95	7.0	1.4	8.0	16.0	Q1
SN74AHC244QPWRG4	TSSOP	PW	20	2000	330.0	16.4	6.95	7.0	1.4	8.0	16.0	Q1

PACKAGE MATERIALS INFORMATION

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*All dimensions are nominal

7 III airrioriorio aro mominar											
Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)				
SN74AHC244QDWRG4	SOIC	DW	20	2000	367.0	367.0	45.0				
SN74AHC244QDWRG4Q1	SOIC	DW	20	2000	367.0	367.0	45.0				
SN74AHC244QPWR	TSSOP	PW	20	2000	356.0	356.0	35.0				
SN74AHC244QPWRG4	TSSOP	PW	20	2000	356.0	356.0	35.0				



SMALL OUTLINE PACKAGE



NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

 2. This drawing is subject to change without notice.

 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
- 5. Reference JEDEC registration MO-153.



SMALL OUTLINE PACKAGE



NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SMALL OUTLINE PACKAGE



NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.





SOIC



NOTES:

- 1. All linear dimensions are in millimeters. Dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

 2. This drawing is subject to change without notice.

 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.43 mm per side.
- 5. Reference JEDEC registration MS-013.



SOIC



NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SOIC



NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.



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